



Product data sheet

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MMFTN3019E-MS

Semiconductor Compiance

Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Continuous Gate-Source Voltage	±20V	V
ID	Continuous Drain Current	100	mA
PD	Power Dissipation	150	mW
R _{0JA}	Thermal Resistance from Junction to Ambient	833	°C /W
T _{STG}	Storage Temperature Range	-55 to +150	°C
TJ	Operating Junction Temperature	+150	°C



SOT-523

These ratings are limiting values above which the serviceability of the device may be impaired.

Specification Features:

- Low On-resistance
- Fast Switching Speed
- Low Voltage Drive Makes This Device Ideal for Portable Equipment
- Easily Designed Drive Circuits
- Easy to Parallel
- RoHS Compliant & Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.002g



Electrical Symbol:

Device Marking Code:







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Off Characteristics

Symbol	Parameter	Test Condition	Limits			llait
			Min	Тур	Max	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} =0V, I _D =10uA	30			Volts
I _{GSS}	Gate-Body Leakage	V_{DS} =0V, V_{GS} = \pm 20V			±1	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V			1	μA

On Characteristics

Symbol	Parameter	Test Condition	Limits			llait
		Test Condition	Min	Тур	Мах	Unit
$V_{th(GS)}$	Gate-Threshold Voltage	V _{DS} = 3V, I _D =100uA	0.8		1.5	Volts
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =4V, I _D =10mA			8	Ω
		V _{GS} =2.5V, I _D =1mA			13	Ω
g fs	Forward Trans Conductance	V_{DS} =3V, I_{D} =10mA	20			ms
V _{SD}	Drain-Source Diode Forward Voltage	I _S =115mA, V _{GS} =0V			1.2	V

Dynamic Characteristics

Symbol	Parameter	Test Condition	Limits			llait
		Test Condition	Min	Тур	Мах	Unit
Ciss	Input Capacitance	V _{DS} = 5V V _{GS} = 0V		13		pF
Coss	Output Capacitance			9		pF
Crss	Reverse Transfer Capacitance	f = 1.0MHz		4		pF

Switching Characteristics

Symbol	Parameter	Test Condition	Limits			Unit
		Test Condition	Min	Тур	Мах	
t _{D(on)}	Turn-on Time	V_{DD} =5V, R _L =500 Ω ,		15		nS
t _{D(off)}	Turn-off Time	I_D =10mA, V_{Gs} =5V, R _G = 10Ω		80		nS



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SOT-523 Package Outline



Typical Soldering Pattern:



DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
А	0.70	0.90	0.028	0.035	
A1	0.00	0.10	0.000	0.004	
A2	0.70	0.80	0.028	0.031	
b1	0.15	0.25	0.006	0.010	
b2	0.25	0.35	0.010	0.014	
с	0.10	0.20	0.004	0.008	
D	1.50	1.70	0.059	0.067	
E	0.70	0.90	0.028	0.035	
E1	1.45	1.75	0.057	0.069	
е	0.50	0.50 TYP.		TYP.	
e1	0.90	1.10	0.035	0.043	
L	0.40 REF.		0.016 REF.		
L1	0.10	0.30	0.004	0.012	
θ	O ⁰	8 °	O ⁰	8 °	

NOTES:

Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.



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